

## 1. General description

Dual ultrafast power diode in a TO220 package.

## 2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

## 3. Applications

- Home appliance power supply
- Secondary rectification

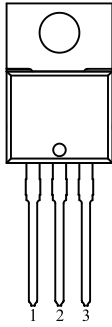
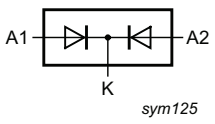
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
<b>Absolute maximum rating</b>						
$V_{RRM}$	repetitive peak reverse voltage		300			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 159$ °C; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	10			A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25$ $\mu$ s; $T_{mb} \leq 159$ °C; square-wave pulse; per diode	20			A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; per diode; <a href="#">Fig. 4</a>	220			A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; per diode	242			A
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; per diode; <a href="#">Fig. 6</a>	-	-	1.25	V
		$I_F = 10$ A; $T_j = 125$ °C; per diode; <a href="#">Fig. 6</a>	-	-	1	V
<b>Dynamic characteristics</b>						
$t_{rr}$	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 100$ A/ $\mu$ s; $T_j = 25$ °C; per diode; <a href="#">Fig. 7</a>	-	-	25	ns

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	K	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV32E-300P	TO220	BYV32E-300PQ	Tube	50	TO220E	26-May-2017

## 7. Marking

Table 4. Marking codes

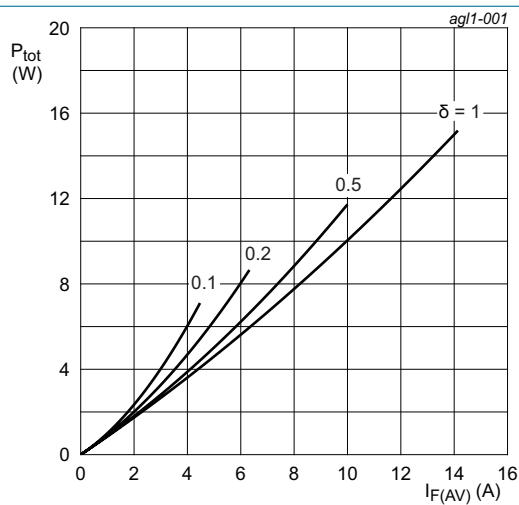
Type number	Marking codes
BYV32E-300P	BYV32E-300P

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

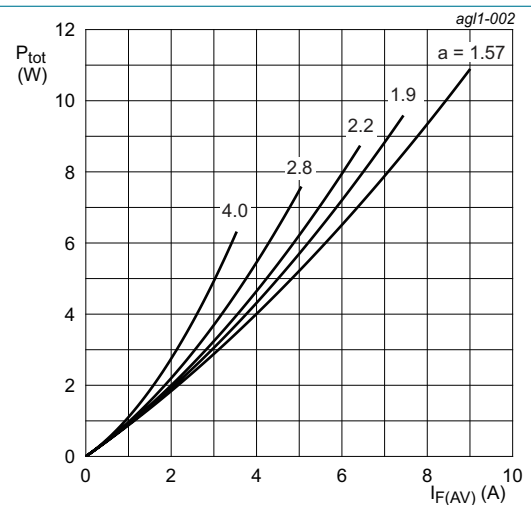
Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		300	V
$V_{RWM}$	crest working reverse voltage		300	V
$V_R$	reverse voltage	DC	300	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 159\text{ }^\circ\text{C}$ ; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	10	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_{mb} \leq 159\text{ }^\circ\text{C}$ ; square-wave pulse; per diode	20	A
$I_{O(AV)}$	average output current	$\delta = 0.5$ ; $T_{mb} \leq 157\text{ }^\circ\text{C}$ ; square-wave pulse; both diodes conducting	20	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode; <a href="#">Fig. 4</a>	220	A
		$t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode	242	A
$T_{stg}$	storage temperature		-65 to 175	$^\circ\text{C}$
$T_j$	junction temperature		175	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 0.836\text{ V}; R_s = 0.0168\text{ }\Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode**



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 0.836\text{ V}; R_s = 0.0168\text{ }\Omega$$

**Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode**

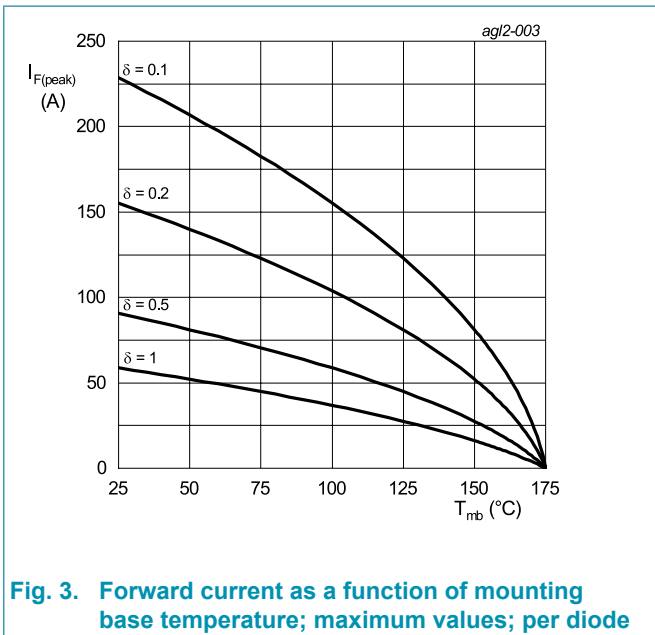


Fig. 3. Forward current as a function of mounting base temperature; maximum values; per diode

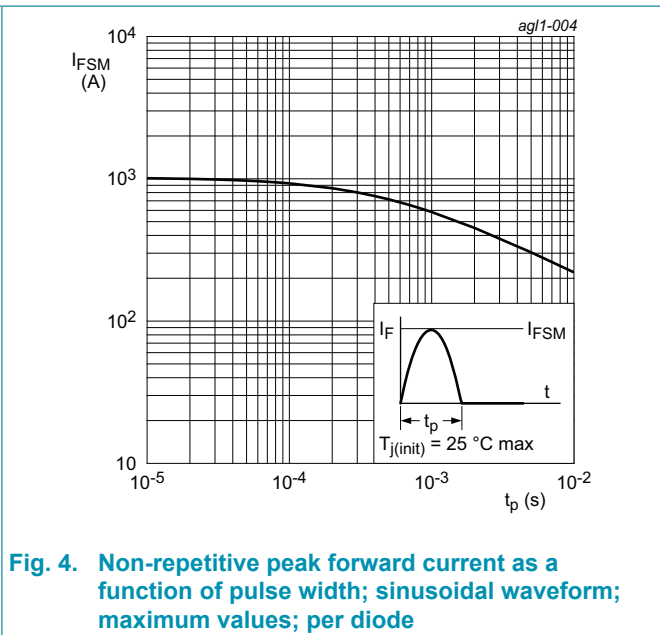


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; <a href="#">Fig. 5</a>	-	-	1.4	K/W
		with heatsink compound; both diodes conducting; <a href="#">Fig. 5</a>	-	-	0.75	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

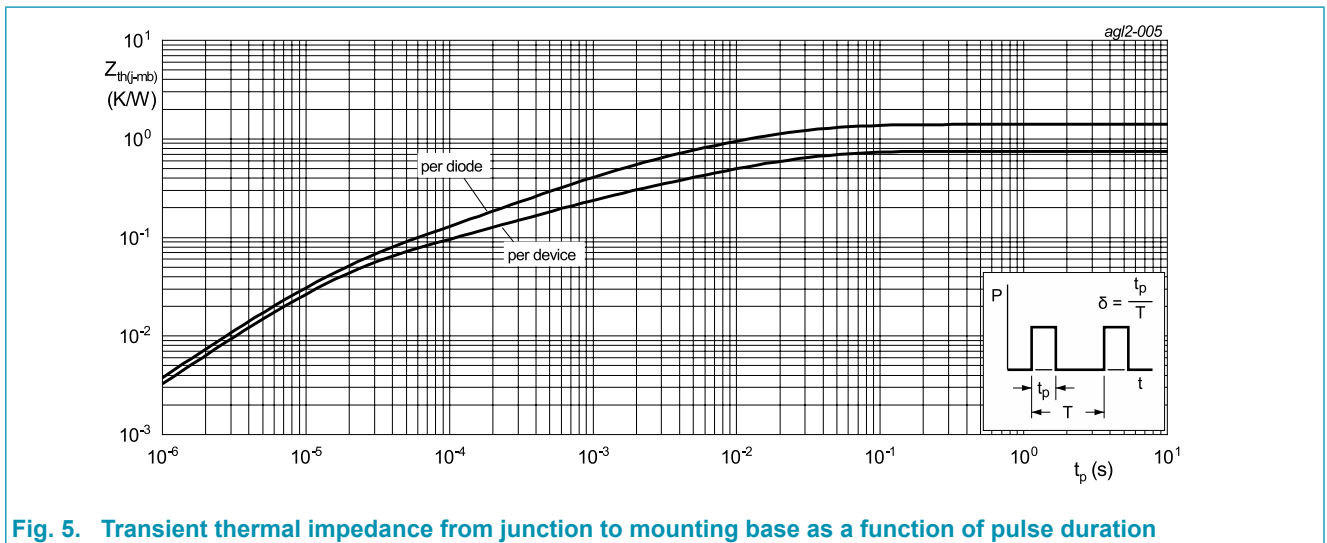
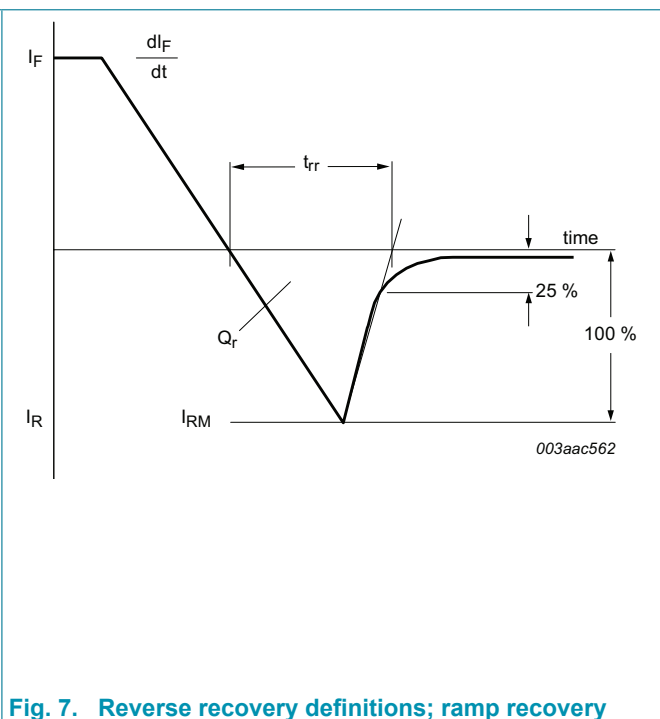
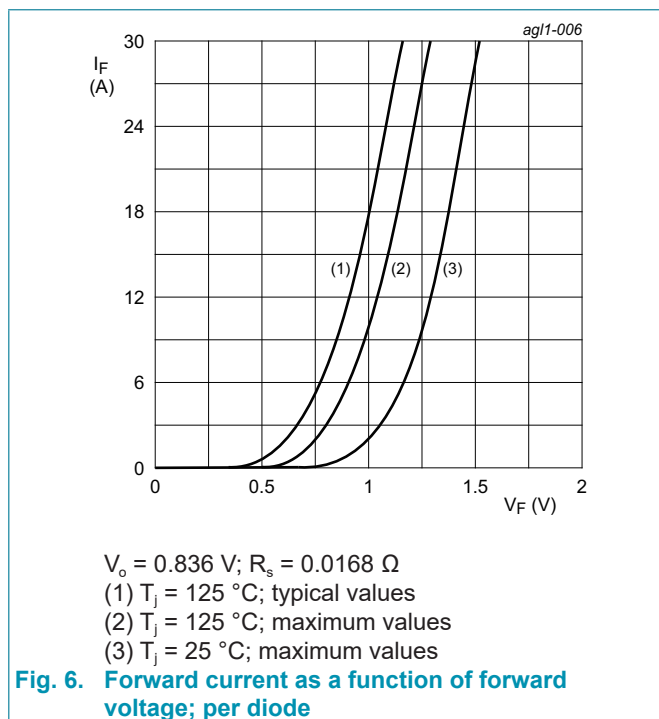


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

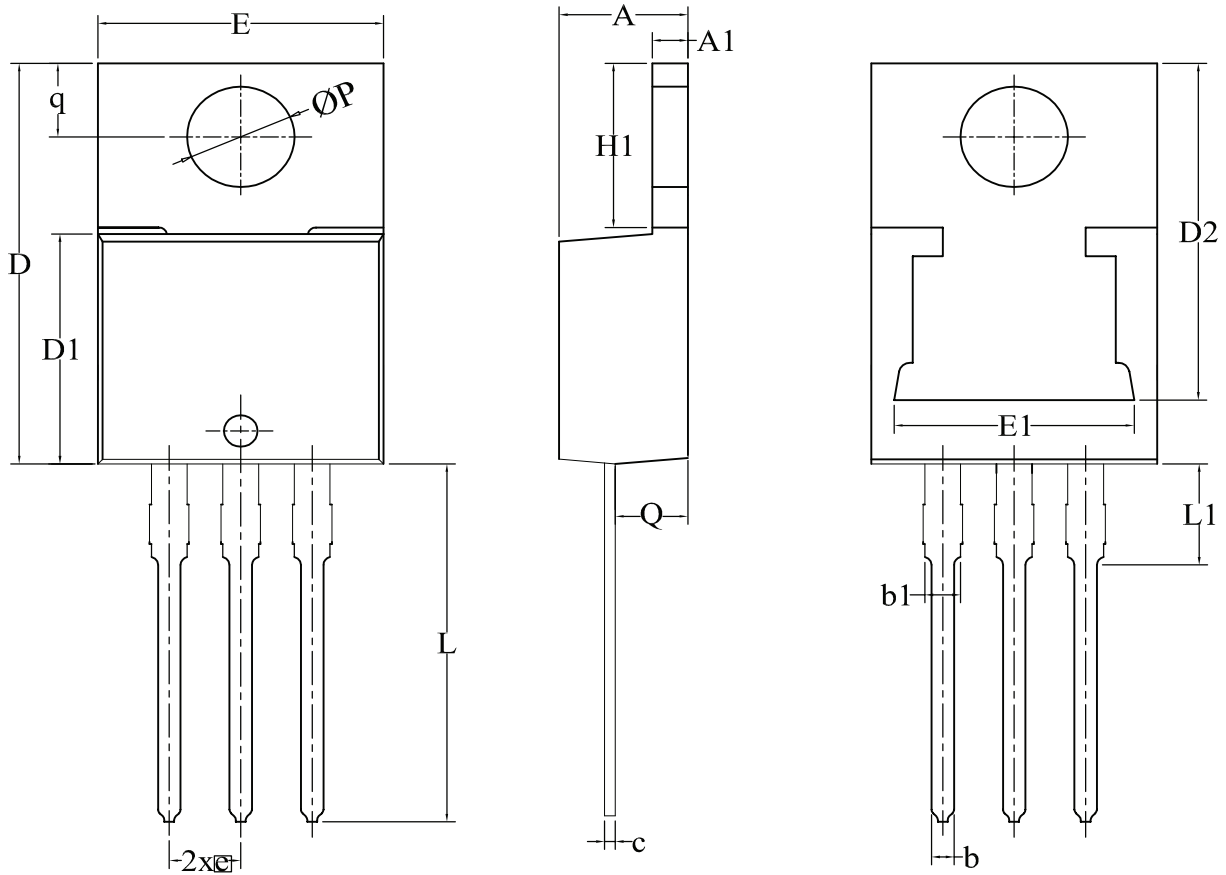
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward current	$I_F = 10\text{ A}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 6</a>	-	-	1.25	V
		$I_F = 10\text{ A}; T_j = 125\text{ °C};$ per diode; <a href="#">Fig. 6</a>	-	-	1	V
$I_R$	reverse current	$V_R = 300\text{ V}; T_j = 25\text{ °C};$ per diode	-	-	20	$\mu\text{A}$
		$V_R = 300\text{ V}; T_j = 125\text{ °C};$ per diode	-	-	300	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$Q_r$	reverse charge	$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 100\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	9	-	nC
$t_{rr}$	reverse recovery time	$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 50\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	-	35	ns
		$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 100\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	-	25	ns
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	25	-	ns
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	33	-	ns
$I_{RM}$	peak reverse recovery current	$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 50\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	0.7	-	A
		$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 100\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	1.1	-	A
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	2.8	-	A
		$I_F = 10\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ per diode; <a href="#">Fig. 7</a>	-	-	8	A



11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3 leads TO-220AB

TO220



Unit	A	A1	b	b1	c	D	D1	D2	E	E1	e	H1	L	L1	P	Q	q
MM	min	4.35	1.14	0.69	1.08	0.36	14.95	8.50	12.20	10.00	8.25	6.00	13.00	3.40	3.70	2.40	2.60
	max	4.75	1.40	1.01	1.67	0.61	15.55	9.02	12.88	10.40	8.89	6.40	14.00	3.80	3.95	2.80	3.00

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## 13. Contents

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1. General description.....	1
2. Features and benefits .....	1
3. Applications .....	1
4. Quick reference data .....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values .....	3
9. Thermal characteristics .....	5
10. Characteristics.....	6
11. Package outline .....	7
12. Legal information .....	8
13. Contents .....	10

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